ABSTRACT

The present invention provides a method for manufacturing a bonded wafer, which includes at least the steps of bonding a bond wafer and a base wafer, grinding an outer peripheral portion of the bonded bond wafer, etching off an unbonded portion of the ground bond wafer, and then reducing a thickness of the bond wafer, wherein, in the step of grinding the outer peripheral portion, the bonded bond wafer is ground so as to form a groove along the outer peripheral portion of the bond wafer to form an outer edge portion outside the groove; and in the subsequent step of etching, the outer edge portion is removed together with the groove portion of the bond wafer to form a terrace portion where the base wafer is exposed at the outer peripheral portion of the bonded wafer. Thus, it is possible to provide a method for manufacturing a bonded wafer, which can reduce the number of dimples formed in a terrace portion of a base wafer upon removing an outer peripheral portion of a bonded bond wafer.